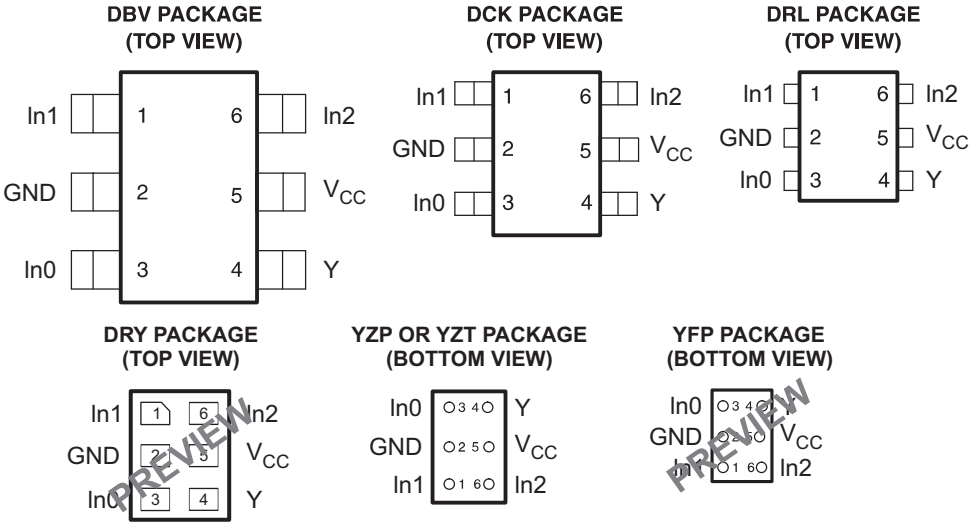
SN74AUP1G58
LOW-POWER CONFIGURABLE MULTIPLE-FUNCTION GATE

SCES504H–NOVEMBER 2003–REVISED DECEMBER 2007

FEATURES

- **Available in the Texas Instruments NanoFree™ Packages**
- **Low Static-Power Consumption (I_{CC} = 0.9 μA Max)**
- **Low Dynamic-Power Consumption (C_{pd} = 4.6 pF Typ at 3.3 V)**
- **Low Input Capacitance (C_i = 1.5 pF Typ)**
- **Low Noise – Overshoot and Undershoot <10% of V_{CC}**
- **I_{off} Supports Partial-Power-Down Mode Operation**
- **Includes Schmitt-Trigger Inputs**
- **Wide Operating V_{CC} Range of 0.8 V to 3.6 V**
- **Optimized for 3.3-V Operation**
- **3.6-V I/O Tolerant to Support Mixed-Mode Signal Operation**
- **t_{pd} = 5.5 ns Max at 3.3 V**
- **Suitable for Point-to-Point Applications**
- **Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II**
- **ESD Performance Tested Per JESD 22**
  - **2000-V Human-Body Model (A114-B, Class II)**
  - **200-V Machine Model (A115-A)**
  - **1000-V Charged-Device Model (C101)**
- **ESD Protection Exceeds ±5000 V With Human-Body Model**



See mechanical drawings for dimensions.

DESCRIPTION/ORDERING INFORMATION

The AUP family is TI's premier solution to the industry's low-power needs in battery-powered portable applications. This family ensures a very low static and dynamic power consumption across the entire V_{CC} range of 0.8 V to 3.6 V, resulting in an increased battery life. This product also maintains excellent signal integrity, which produces very low undershoot and overshoot characteristics.

The SN74AUP1G58 features configurable multiple functions. The output state is determined by eight patterns of 3-bit input. The user can choose the logic functions AND, OR, NAND, NOR, XNOR, inverter, and noninverter. All inputs can be connected to V_{CC} or GND.

The device functions as an independent gate with Schmitt-trigger inputs, which allow for slow input transition and better switching noise immunity at the input.

NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

DESCRIPTION/ORDERING INFORMATION

This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

ORDERING INFORMATION

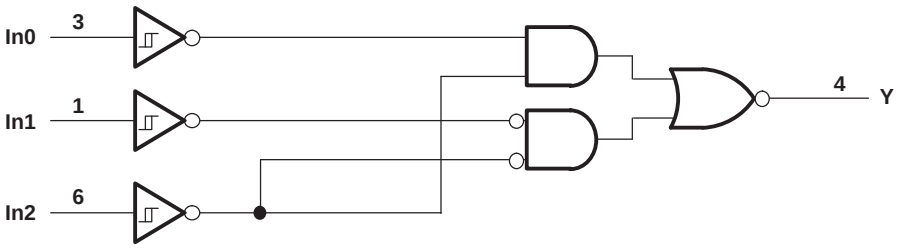
T_A	PACKAGE(1)(2)		ORDERABLE PART NUMBER	TOP-SIDE MARKING(3)
–40°C to 85°C	NanoFree™ – WCSP (DSBGA) 0.23-mm Large Bump – YFP (Pb-free)	Reel of 3000	SN74AUP1G58YFPR	PREVIEW
	NanoFree™ – WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)	Reel of 3000	SN74AUP1G58YZPR	_ _ _HJ_
	NanoFree™ – WCSP (DSBGA) 0.23-mm Large Bump – YZT (Pb-free)	Reel of 3000	SN74AUP1G58YZTR	_ _ _HJ_
	SON – DRY	Reel of 5000	SN74AUP1G58DRYR	PREVIEW
	SOT (SOT-23) – DBV	Reel of 3000	SN74AUP1G58DBVR	H58_
	SOT (SC-70) – DCK	Reel of 3000	SN74AUP1G58DCKR	HJ_
	SOT (SOT-553) – DRL	Reel of 4000	SN74AUP1G58DRLR	

(1) Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.
(2) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.
(3) DBV/DCK/DRL/DRY: The actual top-side marking has one additional character that designates the assembly/test site.
YFP/YZP/YZT: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site. Pin 1 identifier indicates solder-bump composition (1 = SnPb, • = Pb-free).

FUNCTION TABLE

INPUTS			OUTPUT
In2	In1	In0	Y
L	L	L	L
L	L	H	H
L	H	L	L
L	H	H	H
H	L	L	H
H	L	H	H
H	H	L	L
H	H	H	L

LOGIC DIAGRAM (POSITIVE LOGIC)



FUNCTION SELECTION TABLE

LOGIC FUNCTION	FIGURE NO.
2-input AND with inverted input	2, 3
2-input NAND	1
2-input NAND with both inputs inverted	4
2-input OR	4
2-input OR with both inputs inverted	1
2-input NOR with inverted input	2, 3
2-input XOR	5

LOGIC CONFIGURATIONS

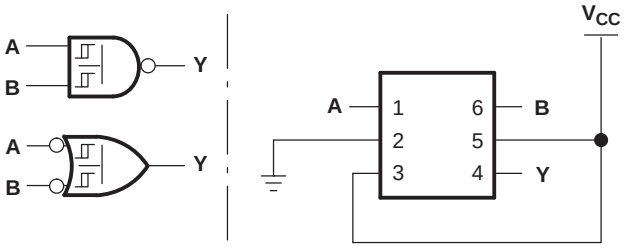


Figure 1. 2-Input NAND Gate

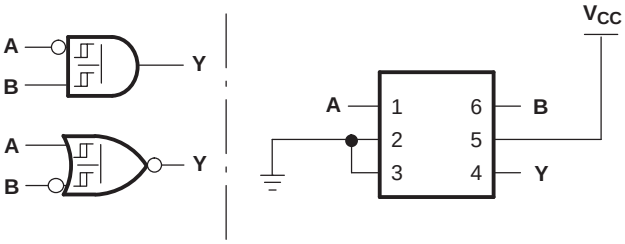


Figure 2. 2-Input AND Gate With Inverted A Input

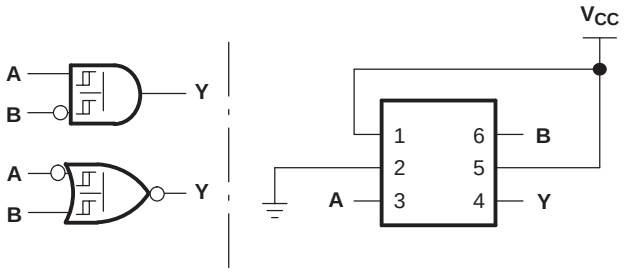


Figure 3. 2-Input AND Gate With Inverted B Input

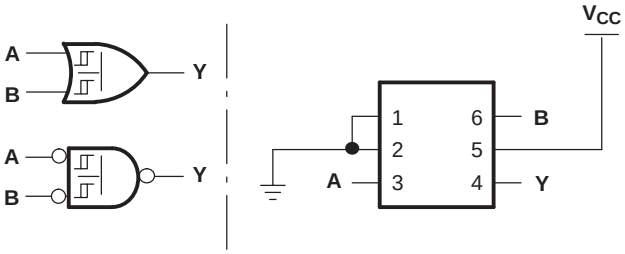


Figure 4. 2-Input OR Gate

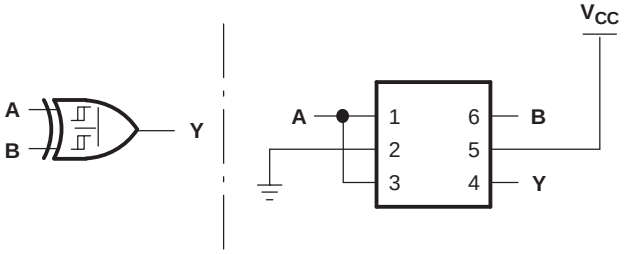


Figure 5. 2-Input XOR Gate

Absolute Maximum Ratings(1)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range		–0.5	4.6	V
V_I	Input voltage range(2)		–0.5	4.6	V
V_O	Voltage range applied to any output in the high-impedance or power-off state(2)		–0.5	4.6	V
V_O	Output voltage range in the high or low state(2)		–0.5	V_{CC} + 0.5	V
I_{IK}	Input clamp current	V_I < 0		–50	mA
I_{OK}	Output clamp current	V_O < 0		–50	mA
I_O	Continuous output current			±20	mA
	Continuous current through V_{CC} or GND			±50	mA
θ_{JA}	Package thermal impedance(3)	DBV package		165	°C/W
		DCK package		259	
		DRL package		142	
		DRY package		234	
		YFP/YZP/YZT package		123	
T_{stg}	Storage temperature range		–65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
(3) The package thermal impedance is calculated in accordance with JESD 51-7.

Recommended Operating Conditions(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		0.8	3.6	V
V_I	Input voltage		0	3.6	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 0.8 V		–20	µA
		V_{CC} = 1.1 V		–1.1	mA
		V_{CC} = 1.4 V		–1.7	
		V_{CC} = 1.65		–1.9	
		V_{CC} = 2.3 V		–3.1	
		V_{CC} = 3 V		–4	
I_{OL}	Low-level output current	V_{CC} = 0.8 V		20	µA
		V_{CC} = 1.1 V		1.1	mA
		V_{CC} = 1.4 V		1.7	
		V_{CC} = 1.65 V		1.9	
		V_{CC} = 2.3 V		3.1	
		V_{CC} = 3 V		4	
T_A	Operating free-air temperature		–40	85	°C

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARMETER	TEST CONDITIONS	V_{CC}	T_A = 25°C			T_A = –40°C to 85°C		UNIT
			MIN	TYP	MAX	MIN	MAX	
V_{T+} Positive-going input threshold voltage		0.8 V	0.3		0.6	0.3	0.6	V
		1.1 V	0.53		0.9	0.53	0.9	
		1.4 V	0.74		1.11	0.74	1.11	
		1.65 V	0.91		1.29	0.91	1.29	
		2.3 V	1.37		1.77	1.37	1.77	
		3 V	1.88		2.29	1.88	2.29	
$V_{T–}$ Negative-going input threshold voltage		0.8 V	0.1		0.6	0.1	0.6	V
		1.1 V	0.26		0.65	0.26	0.65	
		1.4 V	0.39		0.75	0.39	0.75	
		1.65 V	0.47		0.84	0.47	0.84	
		2.3 V	0.69		1.04	0.69	1.04	
		3 V	0.88		1.24	0.88	1.24	
ΔV_T Hysteresis ($V_{T+} – V_{T–}$)		0.8 V	0.07		0.5	0.07	0.5	V
		1.1 V	0.08		0.46	0.08	0.46	
		1.4 V	0.18		0.56	0.18	0.56	
		1.65 V	0.27		0.66	0.27	0.66	
		2.3 V	0.53		0.92	0.53	0.92	
		3 V	0.79		1.31	0.79	1.31	
V_{OH}	I_{OH} = –20 µA	0.8 V to 3.6 V	V_{CC} – 0.1			V_{CC} – 0.1		V
	I_{OH} = –1.1 mA	1.1 V	0.75 × V_{CC}			0.7 × V_{CC}		
	I_{OH} = –1.7 mA	1.4 V	1.11			1.03		
	I_{OH} = –1.9 mA	1.65 V	1.32			1.3		
	I_{OH} = –2.3 mA	2.3 V	2.05			1.97		
	I_{OH} = –3.1 mA		1.9			1.85		
	I_{OH} = –2.7 mA	3 V	2.72			2.67		
	I_{OH} = –4 mA		2.6			2.55		
V_{OL}	I_{OL} = 20 µA	0.8 V to 3.6 V			0.1		0.1	V
	I_{OL} = 1.1 mA	1.1 V			0.3 × V_{CC}		0.3 × V_{CC}	
	I_{OL} = 1.7 mA	1.4 V			0.31		0.37	
	I_{OL} = 1.9 mA	1.65 V			0.31		0.35	
	I_{OL} = 2.3 mA	2.3 V			0.31		0.33	
	I_{OL} = 3.1 mA				0.44		0.45	
	I_{OL} = 2.7 mA	3 V			0.31		0.33	
	I_{OL} = 4 mA				0.44		0.45	
I_I All inputs	V_I = GND to 3.6 V	0 V to 3.6 V			0.1		0.5	µA
I_{off}	V_I or V_O = 0 V to 3.6 V	0 V			0.2		0.6	µA
ΔI_{off}	V_I or V_O = 0 V to 3.6 V	0 V to 0.2 V			0.2		0.6	µA
I_{CC}	V_I = GND or (V_{CC} to 3.6 V), I_O = 0	0.8 V to 3.6 V			0.5		0.9	µA
ΔI_{CC}	V_I = V_{CC} – 0.6 V(1), I_O = 0	3.3 V			40		50	µA
C_i	V_I = V_{CC} or GND	0 V		1.5				pF
		3.6 V		1.5				
C_o	V_O = GND	0 V		3				pF

(1) One input at V_{CC} – 0.6 V, other inputs at V_{CC} or GND

Switching Characteristics

over recommended operating free-air temperature range, C_L = 5 pF (unless otherwise noted) (see Figure 6 and Figure 7)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC}	T_A = 25°C			T_A = –40°C to 85°C		UNIT
				MIN	TYP	MAX	MIN	MAX	
t_{pd}	In0, In1, or In2	Y	0.8 V		23.6				ns
			1.2 V ± 0.1 V	2.8	9.4	13.8	2.3	17.4	
			1.5 V ± 0.1 V	2.1	6.5	9.2	1.6	11.3	
			1.8 V ± 0.15 V	1.5	5.4	7.4	1	9	
			2.5 V ± 0.2 V	1.1	4	5.6	0.6	6.6	
			3.3 V ± 0.3 V	1	3.2	4.6	0.5	5.5	

Switching Characteristics

over recommended operating free-air temperature range, C_L = 10 pF (unless otherwise noted) (see Figure 6 and Figure 7)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC}	T_A = 25°C			T_A = –40°C to 85°C		UNIT
				MIN	TYP	MAX	MIN	MAX	
t_{pd}	In0, In1, or In2	Y	0.8 V		26.4				ns
			1.2 V ± 0.1 V	3.2	10.7	15.2	2.7	19	
			1.5 V ± 0.1 V	2	7.5	10.5	1.5	12.5	
			1.8 V ± 0.15 V	1.1	6.2	8.4	0.6	10.2	
			2.5 V ± 0.2 V	1	4.6	6.4	0.5	7.6	
			3.3 V ± 0.3 V	1	3.7	5.3	0.5	6.3	

Switching Characteristics

over recommended operating free-air temperature range, C_L = 15 pF (unless otherwise noted) (see Figure 6 and Figure 7)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC}	T_A = 25°C			T_A = –40°C to 85°C		UNIT
				MIN	TYP	MAX	MIN	MAX	
t_{pd}	In0, In1, or In2	Y	0.8 V		29.6				ns
			1.2 V ± 0.1 V	3.8	11.8	16.8	3.3	21.1	
			1.5 V ± 0.1 V	2.9	8.3	11.6	2.4	13.8	
			1.8 V ± 0.15 V	2.2	6.8	9.3	1.7	11.3	
			2.5 V ± 0.2 V	1.7	5.1	7	1.2	8.4	
			3.3 V ± 0.3 V	1.4	4.2	5.9	0.9	7	

Switching Characteristics

over recommended operating free-air temperature range, C_L = 30 pF (unless otherwise noted) (see Figure 6 and Figure 7)

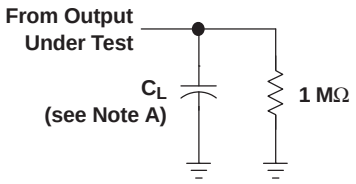
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC}	T_A = 25°C			T_A = –40°C to 85°C		UNIT
				MIN	TYP	MAX	MIN	MAX	
t_{pd}	In0, In1, or In2	Y	0.8 V		38.1				ns
			1.2 V ± 0.1 V	5.1	15	21.4	4.6	26.6	
			1.5 V ± 0.1 V	4	10.6	14.6	3.5	17.4	
			1.8 V ± 0.15 V	3.2	8.7	11.7	2.7	14.2	
			2.5 V ± 0.2 V	2.5	6.5	8.7	2	10.5	
			3.3 V ± 0.3 V	2.1	5.4	7.3	1.6	8.7	

Operating Characteristics

T_A = 25°C

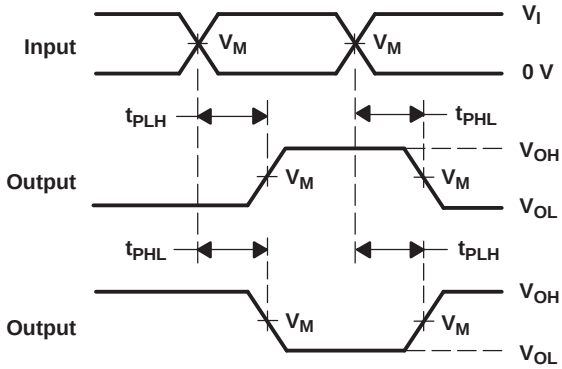
PARAMETER		TEST CONDITIONS	V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance	f = 10 MHz	0.8 V	4	pF
			1.2 V ± 0.1 V	4	
			1.5 V ± 0.1 V	4	
			1.8 V ± 0.15 V	4	
			2.5 V ± 0.2 V	4.3	
			3.3 V ± 0.3 V	4.6	

PARAMETER MEASUREMENT INFORMATION
(Propagation Delays, Setup-and-Hold Times, and Pulse Duration)

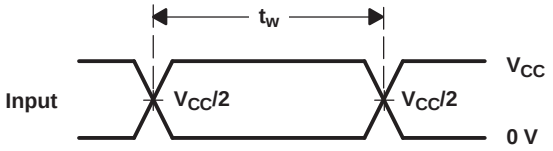


LOAD CIRCUIT

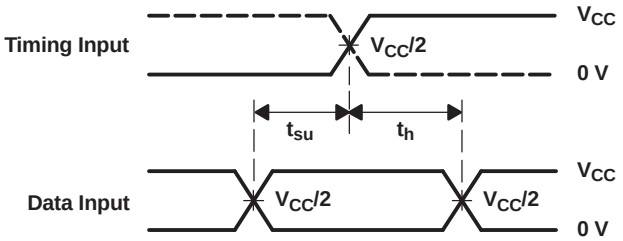
	V_{CC} = 0.8 V	V_{CC} = 1.2 V ± 0.1 V	V_{CC} = 1.5 V ± 0.1 V	V_{CC} = 1.8 V ± 0.15 V	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V
C_L	5, 10, 15, 30 pF	5, 10, 15, 30 pF	5, 10, 15, 30 pF	5, 10, 15, 30 pF	5, 10, 15, 30 pF	5, 10, 15, 30 pF
V_M	$V_{CC}/2$	$V_{CC}/2$	$V_{CC}/2$	$V_{CC}/2$	$V_{CC}/2$	$V_{CC}/2$
V_I	V_{CC}	V_{CC}	V_{CC}	V_{CC}	V_{CC}	V_{CC}



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
PULSE DURATION

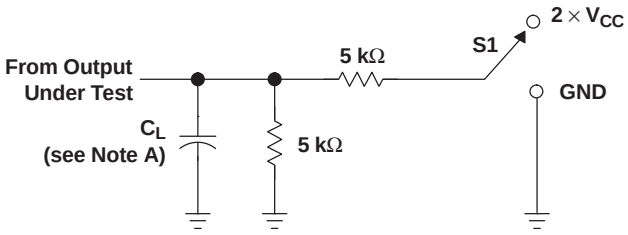


VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, slew rate ≥ 1 V/ns.
C. The outputs are measured one at a time, with one transition per measurement.
D. t_{PLH} and t_{PHL} are the same as t_{pd}.
E. All parameters and waveforms are not applicable to all devices.

Figure 6. Load Circuit and Voltage Waveforms

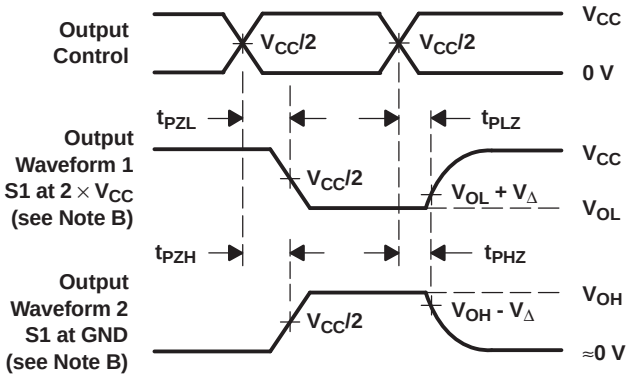
PARAMETER MEASUREMENT INFORMATION
(Enable and Disable Times)



LOAD CIRCUIT

TEST	S1
t_{PLZ}/t_{PZL} t_{PHZ}/t_{PZH}	$2 \times V_{CC}$ GND

	V_{CC} = 0.8 V	V_{CC} = 1.2 V ± 0.1 V	V_{CC} = 1.5 V ± 0.1 V	V_{CC} = 1.8 V ± 0.15 V	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V
C_L	5, 10, 15, 30 pF	5, 10, 15, 30 pF	5, 10, 15, 30 pF	5, 10, 15, 30 pF	5, 10, 15, 30 pF	5, 10, 15, 30 pF
V_M	$V_{CC}/2$	$V_{CC}/2$	$V_{CC}/2$	$V_{CC}/2$	$V_{CC}/2$	$V_{CC}/2$
V_I	V_{CC}	V_{CC}	V_{CC}	V_{CC}	V_{CC}	V_{CC}
V_Δ	0.1 V	0.1 V	0.1 V	0.15 V	0.15 V	0.3 V



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, slew rate ≥ 1 V/ns.
D. The outputs are measured one at a time, with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. All parameters and waveforms are not applicable to all devices.

Figure 7. Load Circuit and Voltage Waveforms

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)
SN74AUP1G58DBVR	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74AUP1G58DBVRE4	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74AUP1G58DBVRG4	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74AUP1G58DBVT	ACTIVE	SOT-23	DBV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74AUP1G58DBVTE4	ACTIVE	SOT-23	DBV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74AUP1G58DBVTG4	ACTIVE	SOT-23	DBV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74AUP1G58DCKR	ACTIVE	SC70	DCK	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74AUP1G58DCKRE4	ACTIVE	SC70	DCK	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74AUP1G58DCKRG4	ACTIVE	SC70	DCK	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74AUP1G58DCKT	ACTIVE	SC70	DCK	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74AUP1G58DCKTE4	ACTIVE	SC70	DCK	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74AUP1G58DCKTG4	ACTIVE	SC70	DCK	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74AUP1G58DRLR	ACTIVE	SOT	DRL	6	4000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74AUP1G58DRLRG4	ACTIVE	SOT	DRL	6	4000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74AUP1G58YZPR	ACTIVE	WCSP	YZP	6	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM
SN74AUP1G58YZTR	ACTIVE	DSBGA	YZT	6	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

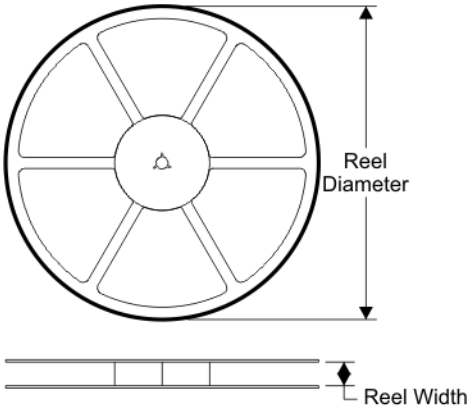
(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

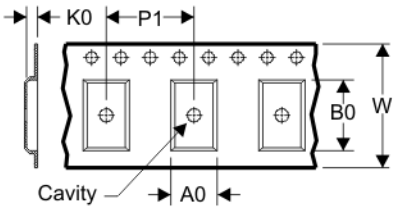
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL BOX INFORMATION

REEL DIMENSIONS

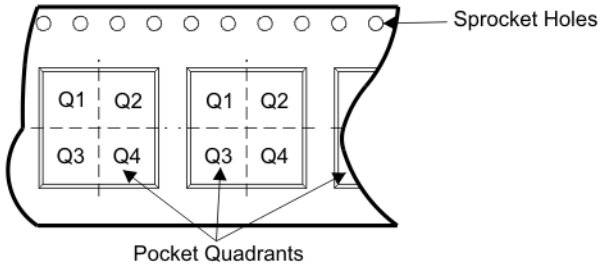


TAPE DIMENSIONS



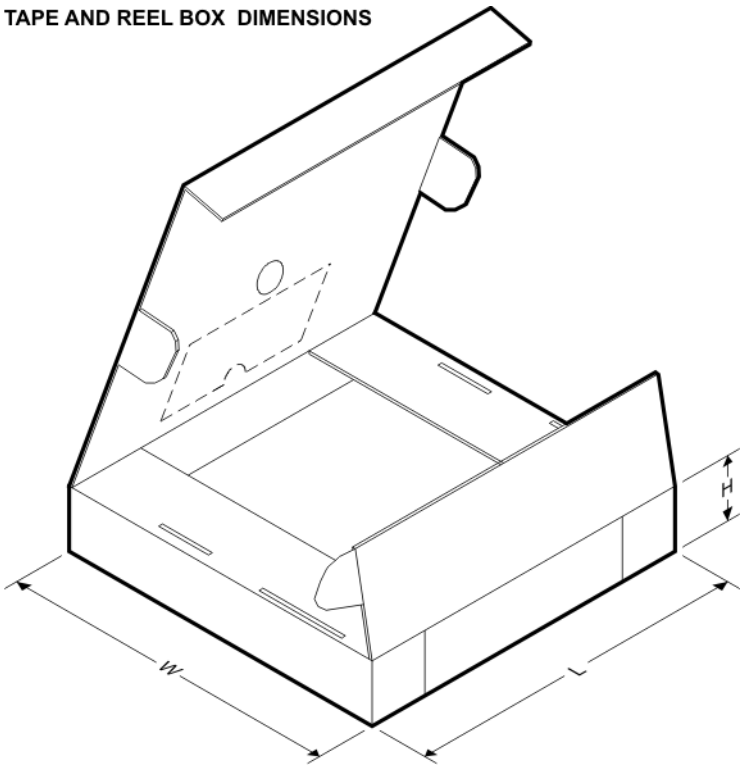
A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



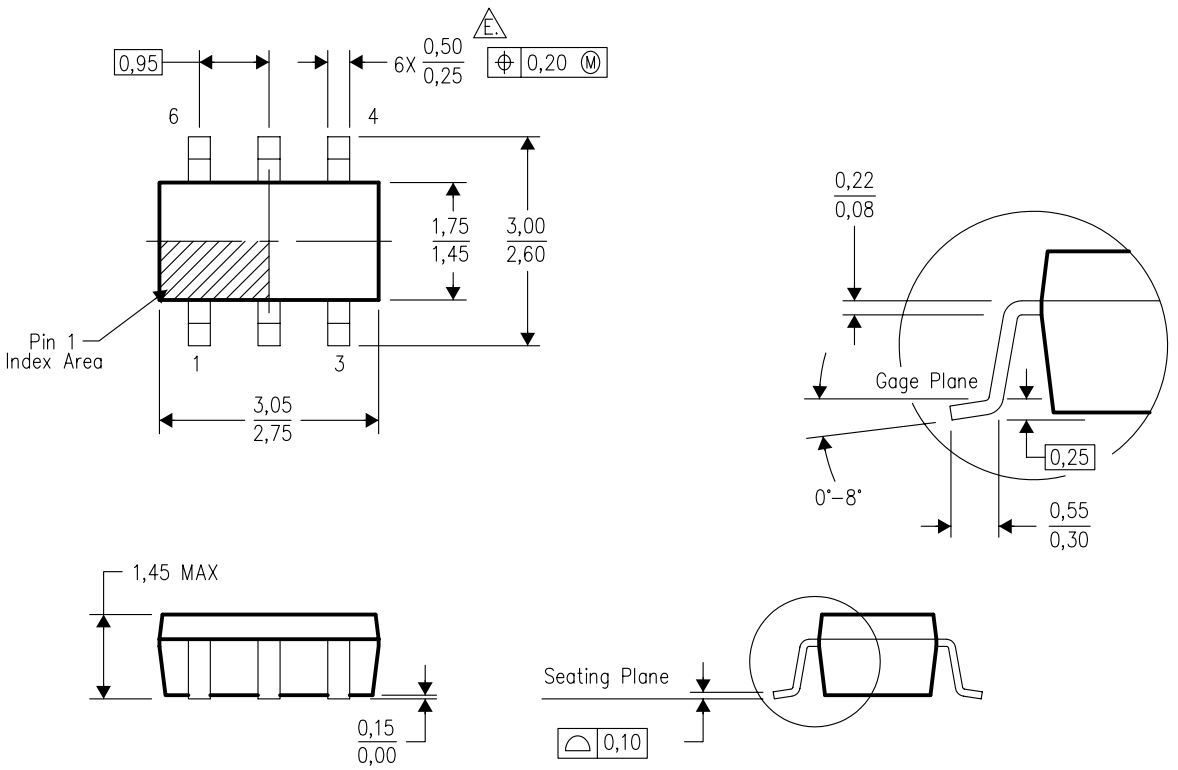
Device	Package	Pins	Site	Reel Diameter (mm)	Reel Width (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AUP1G58DBVR	DBV	6	SITE 35	180	9	3.23	3.17	1.37	4	8	Q3
SN74AUP1G58DBVT	DBV	6	SITE 35	180	9	3.23	3.17	1.37	4	8	Q3
SN74AUP1G58DCKR	DCK	6	SITE 35	180	9	2.24	2.34	1.22	4	8	Q3
SN74AUP1G58DCKT	DCK	6	SITE 35	180	9	2.24	2.34	1.22	4	8	Q3
SN74AUP1G58DRLR	DRL	6	SITE 35	180	9	1.78	1.78	0.69	4	8	Q3
SN74AUP1G58YZPR	YZP	6	SITE 12	180	8	1.02	1.52	0.66	4	8	Q1
SN74AUP1G58YZTR	YZT	6	SITE 12	0	0	1.1	1.6	0.7	4	8	Q1

TAPE AND REEL BOX DIMENSIONS



Device	Package	Pins	Site	Length (mm)	Width (mm)	Height (mm)
SN74AUP1G58DBVR	DBV	6	SITE 35	202.0	201.0	28.0
SN74AUP1G58DBVT	DBV	6	SITE 35	202.0	201.0	28.0
SN74AUP1G58DCKR	DCK	6	SITE 35	202.0	201.0	28.0
SN74AUP1G58DCKT	DCK	6	SITE 35	202.0	201.0	28.0
SN74AUP1G58DRLR	DRL	6	SITE 35	202.0	201.0	28.0
SN74AUP1G58YZPR	YZP	6	SITE 12	220.0	220.0	0.0
SN74AUP1G58YZTR	YZT	6	SITE 12	220.0	220.0	0.0

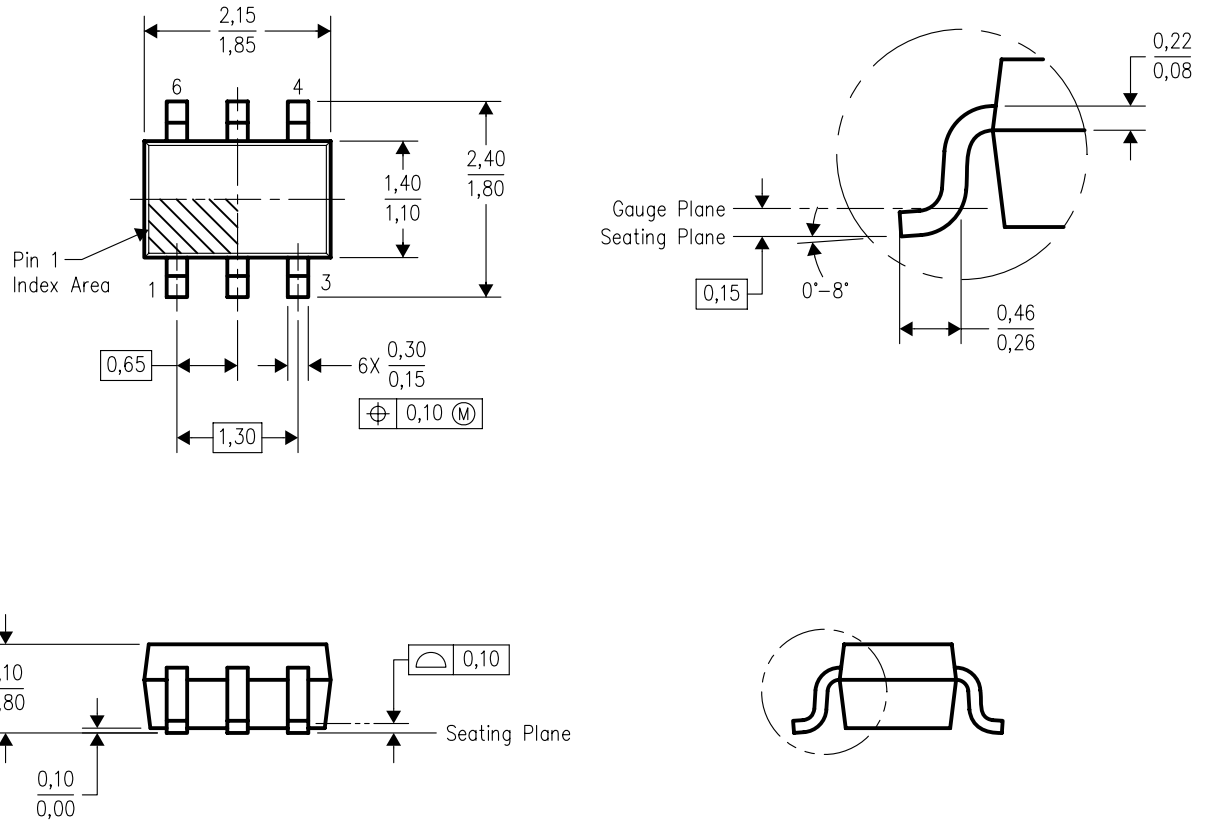
DBV (R–PDSO–G6) PLASTIC SMALL–OUTLINE PACKAGE



4073253–5/K 03/2006

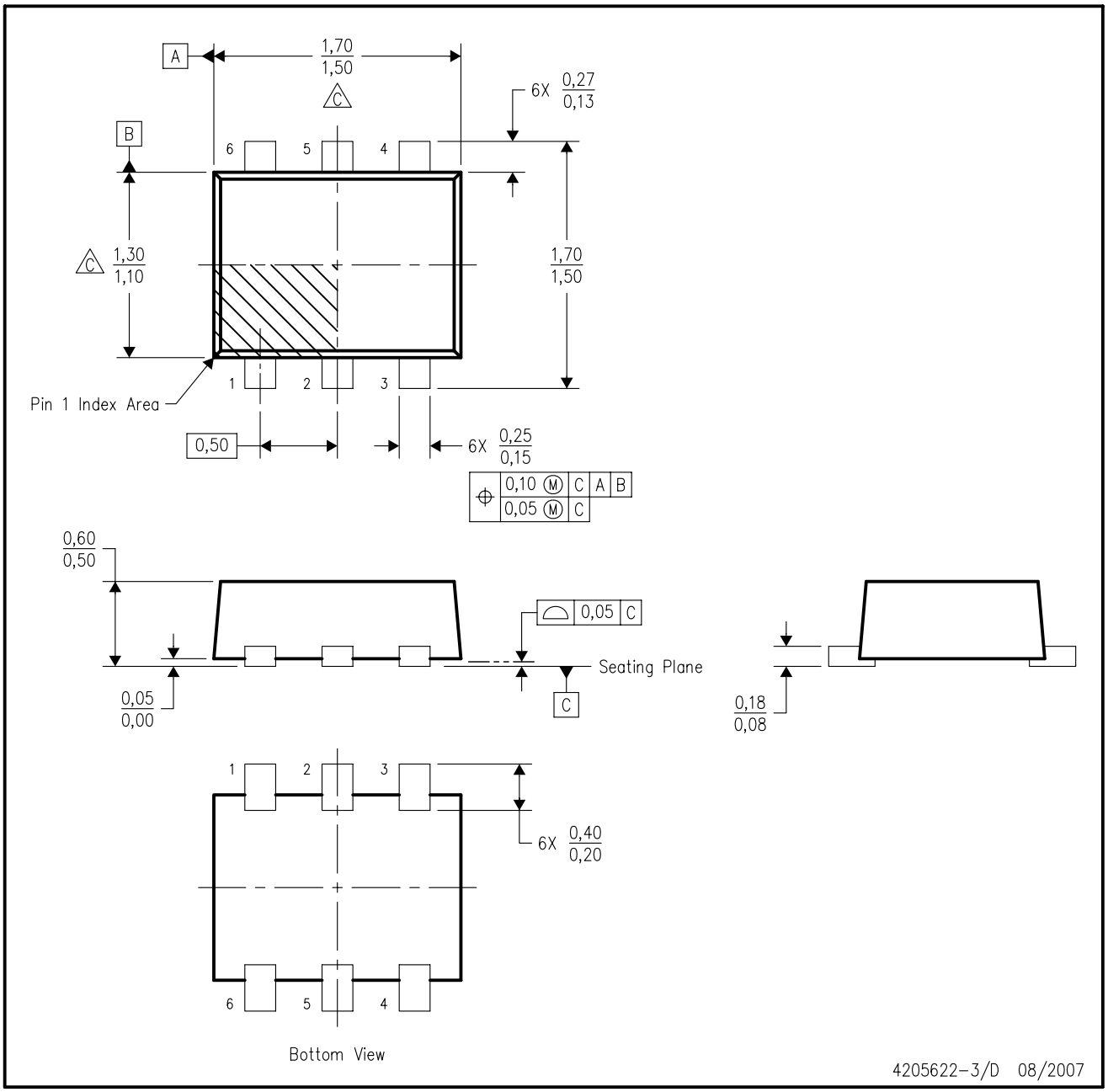
NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
D. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
E. Falls within JEDEC MO–178 Variation AB, except minimum lead width.

DCK (R–PDSO–G6) PLASTIC SMALL–OUTLINE PACKAGE



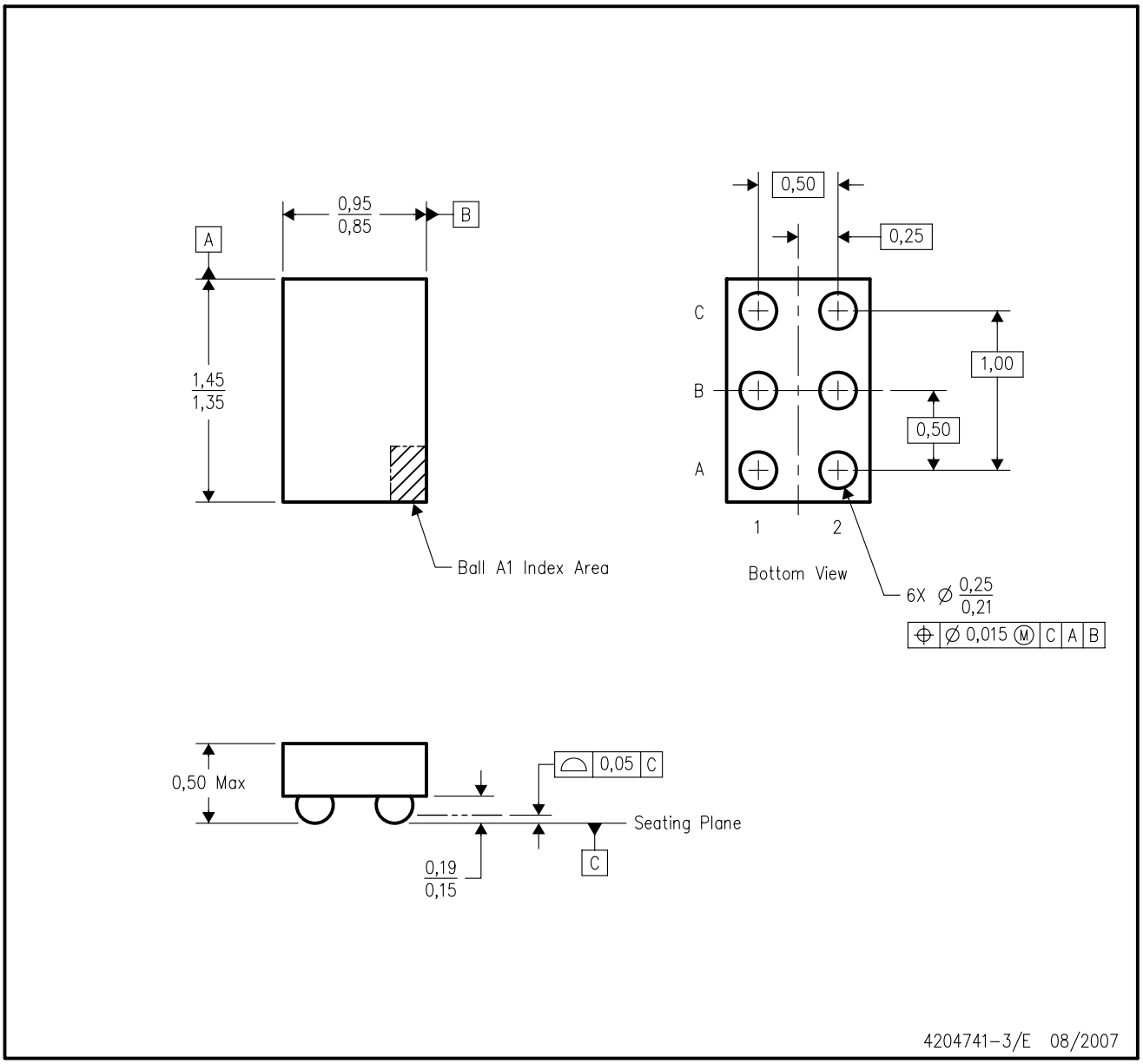
4093553–4/G 01/2007

NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
D. Falls within JEDEC MO–203 variation AB.



NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash, interlead flash, protrusions, or gate burrs. Mold flash, interlead flash, protrusions, or gate burrs shall not exceed 0,15 per end or side.
D. JEDEC package registration is pending.

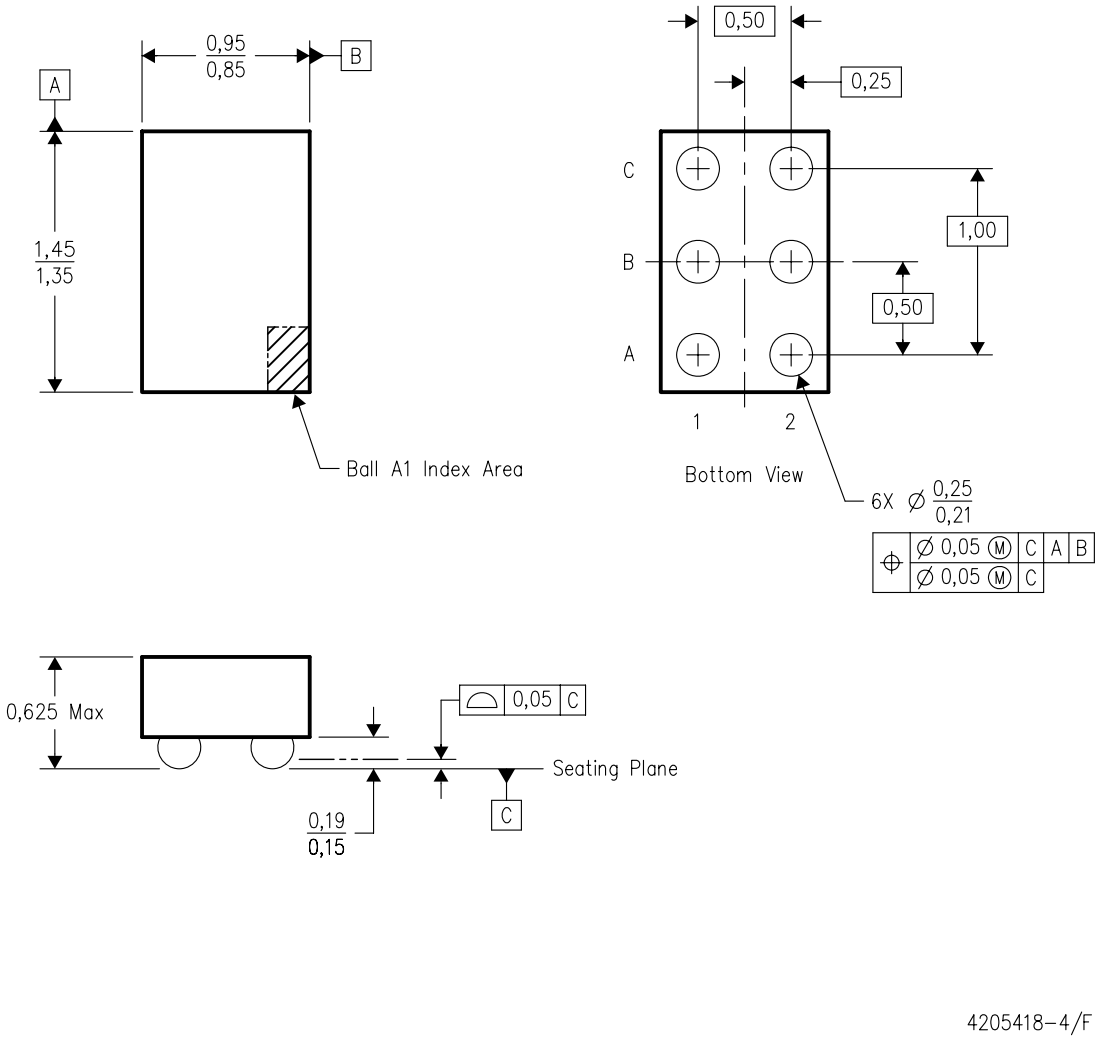
YZP (R–XBGA–N6) DIE–SIZE BALL GRID ARRAY



NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. NanoFree™ package configuration.
D. This package is lead–free. Refer to the 6 YEP package (drawing 4204725) for tin–lead (SnPb).

NanoFree is a trademark of Texas Instruments.

YZT (R–XBGA–N6) DIE–SIZE BALL GRID ARRAY



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. NanoFree™ package configuration.
D. This package is Lead–free. Refer to the 6 YET package (drawing 4205421) for tin–lead (SnPb).

NanoFree is a trademark of Texas Instruments.